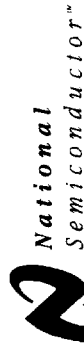


PNP Transistors

Discrete POWER & Signal Technologies

PNP Medium Power



Device No.	Case Style	V _{CB0} (V) Min	V _{CEO} (V) Min	V _{EBO} (V) Min	I _{CB0} (nA) @ V _{CB} (V) Max	h _{FE} @ I _C & V _{CE} (V) Min Max	V _{CE(SAT)} V _{BE(SAT)} (V) & (V) Max Max	I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Max	t _{on} (ns) Max	NF (dB) Max	Test Conditions	Process No.
MPS855	TO-92 (92)	40	25	6	100 35	45 85 40 300 100 800	0.5 1.2 800 0.5 1 1	5 100 800	15	100	50				60 (5-157)
MPS6562	TO-92 (92)	25	25	5	100 20	50 200 50 50 100 10 35	0.5 500 1 0.5 100 1 1	500 500 10	30	60	10				67
PN4355	TO-92 (92)	60	60	5	50 50	75 75 100 75 60 500 100 400 10 0.1	0.15 0.9 150 0.5 1.1 500	150 500 500	30	100	500 50	400	3		67
PN4356	TO-92 (92)	80	80	5	50 50	30 40 50 250 40 25 500 100 10 1 0.1	0.15 0.9 150 0.5 1.1 500	150 500 500	30	100	500 50	400	3		67
TN4033A	TO-226 (99)	80	80	5	50 60	75 100 70 25 0.1 300 500 1A	0.15 0.9 150 0.5 500	150 500 500	20	150	500 50	400		(Note 1)	67 (5-78)
TN5322A	TO-226 (99)		75			30 10 100 130 500 1A	0.7 500 4 2	500 500 500		50	50	100		(Note 1)	71
MPSA55	TO-92 (92)		60	4	100 60	100 100 100 100 10 1	0.25 100 1 1	100 100 100		50	100				73
MPSA56	TO-92 (92)		80	4	100 80	100 100 100 100 10 1	0.25 100 1 1	100 100 100		50	100				73 (5-178)

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device datasheet.

PNP Medium Power (continued)

Device No.	Case Style	V _{CBO} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CBO} (nA) @ V _{CB} (V) Max	h _{FE} @ I _C & V _{CE} (mA) (V) Min Max	V _{CE(SAT)} (V) & V _{BE(SAT)} (V) @ I _C (mA) Max Min Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) @ Max	t _(off) (ns) Max	Test Conditions	Process No.
MPSA92	TO-92 (92)	300	300	5	250 200	25 40 25 1 10 30 Max	0.5 0.9 20	6	50	10			76 (5-186)
MPSA93	TO-92 (92)	200	200	5	250 160	25 40 25 1 10 30 Max	0.4 0.9 20	8	50	10			76
TN5415A	TO-226 (99)	200	200	4	50K 175	30 150 50 10 10 10 Max	2.5 50 10	15	15	5			76
TN6726A	TO-226 (99)	40	30	5	100 40	55 60 50 10 100 200 Max	0.5 1A 250	30	50	50			77 (5-138)
TN6728A	TO-226 (99)	60	60	5	100 40	80 50 20 50 250 500 Max	0.35 250 1	30	50	50			78 (5-142)
TN6729A	TO-226 (99)	80	80	5	100 60	80 50 20 50 250 500 Max	0.35 250 1	30	50	50			79 (5-146)

TEST CONDITIONS

Note 1: I_C = 500 mA, I_B 1/30 mA.

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (**section-page**) of process characteristics.